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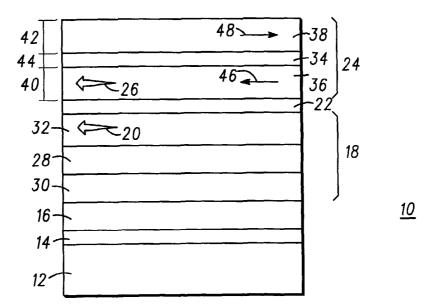
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- (71) Applicant (for all designated States except US): FREESCALE SEMICONDUCTOR, INC. [US/US]; 6501 William Cannon Drive West, Austin, TX 78735 (US).
- (72) Inventors; and
- (75) Inventors/Applicants (for US only): JANESKY, Jason, A. [US/US]; 935 N. Whalers Cove Dr., Gilbert, AZ 85234 (US). ENGEL, Bradley, N. [US/US]; 5651 W. Gail Drive, Chandler, AZ 85226 (US). SLAUGHTER, Jon, M. [US/US]; 9251 South Kenneth Place, Tempe, AZ 85284 (US).

- (74) Agents: KING, Robert, L. et al.; Corporate Law Department, Intellectual Property Section, 7700 West Parmer Lane, MD: TX32/PL02, Austin, TX 78729 (US).
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[Continued on next page]

(54) Title: MAGNETORESISTIVE RANDOM ACCESS MEMORY WITH REDUCED SWITCHING FIELD VARIATION



(57) Abstract: An array of multi-state, multi-layer magnetic memory devices (10) wherein each memory device comprises a non-magnetic spacer region (22) and a free magnetic region (24) positioned adjacent to a surface of the nonmagnetic spacer region, the free magnetic region including a plurality of magnetic layers (36, 34, 38), wherein the magnetic layer (36) in the plurality of magnetic layers positioned adjacent to the surface of the nonmagnetic spacer region has a thickness substantially greater than a thickness of each of the magnetic layers (34, 38) subsequently grown thereon wherein the thickness is chosen to improve the magnetic switching variation so that the magnetic switching field for each memory device in the array of memory devices is more uniform.

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C. DOCUMENTS CONSIDERED TO BE RELEVANT			
Category *	Citation of document, with indication, where ap		Relevant to claim No.
X	US 6,166,948 A (Parkin et al.) 26 December 2000 (2	1,5-11,12,14	
Y	lines 31-33, lines 58-61, column 7 line 49 2-4,13		
Х	US 6,545,906 B1 (Savtchenko et al) 08 April 2003 (6 2 lines 30-40 column 5 lines 47-57	1,6-11	
х			
 Y	13,column 3 line 45-50		2-4,15-32
Υ	US 6,205,052 B1 (Slaughter et al.) 20 March 2001(20.03.2001), abstract, Column 7 line 7-8		3,4
Further	documents are listed in the continuation of Box C.	See patent family annex.	
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P.O. Box 1450 Alexandria, Virginia 22313-1450		Telephone No. 571-272-1790	
	. (703)305-3230		